

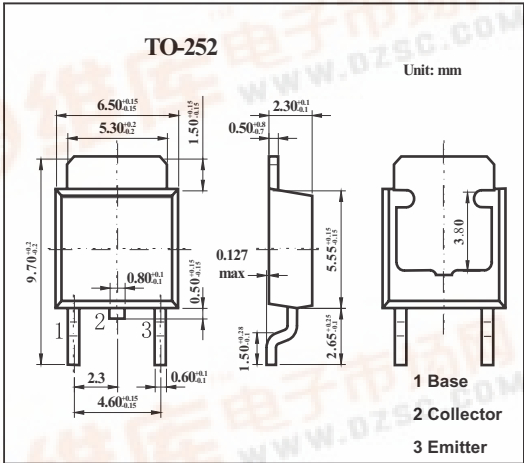
SMD Type

Transistors

High-Current Switching Applications
2SB1203

■ Features

- Low collector-to-emitter saturation voltage.
- High current and high f_T .
- Excellent linearity of h_{FE} .
- Fast switching speed.

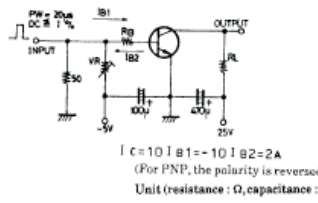


■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CB0}	-60	V
Collector-emitter voltage	V_{CE0}	-50	V
Emitter-base voltage	V_{EB0}	-6	V
Collector current	I_C	-5	A
Collector current (pulse)	I_{CP}	-8	A
Collector dissipation $T_c = 25^\circ\text{C}$	P_C	1	W
		20	W
Jumction temperature	T_J	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

2SB1203

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector cutoff current	ICBO	V _{CB} = -40V, I _E = 0			-1	μA
Emitter cutoff current	IEBO	V _{EB} = -4V, I _C = 0			-1	μA
DC current Gain	h _{FE}	V _{CE} = -2V, I _C = -0.5A	70		400	
		V _{CE} = -2V, I _C = -4A	35			
Gain bandwidth product	f _T	V _{CE} = -5V, I _C = -1A		130		MHz
Output capacitance	C _{ob}	V _{CB} = -10V, f = 1MHz		60		pF
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = -3A, I _B = -0.15A		-280	-550	mV
Base-to-emitter saturation voltage	V _{BE(sat)}	I _C = -3A, I _B = -0.15A		-0.95	-1.3	V
Collector-to-base breakdown voltage	V _{(BR)CBO}	I _C = -10μA, I _E = 0	-60			V
Collector-to-emitter breakdown voltage	V _{(BR)CEO}	I _C = -1mA, R _{BE} = ∞	-50			V
Emitter-to-base breakdown voltage	V _{(BR)EBO}	I _E = -10μA, I _C = 0	-6			V
Turn-on time	t _{on}	 $I_C = 10\text{mA}$ $I_{B1} = -10\text{mA}$ $I_{B2} = 2\text{A}$ (For PNP, the polarity is reversed.) Unit (resistance: Ω, capacitance: F)		50		ns
Storage time	t _{stg}			450		ns
Fall time	t _f			20		ns

■ h_{FE} Classification

Rank	Q	R	S	T
h _{FE}	70~140	100~200	140~280	200~400